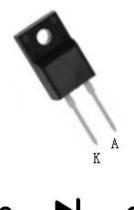


## FRED Ultrafast Soft Recovery Diode, 30A

#### **Features:**

- Ultrafast Recovery
- 175°C operating junction temperature
- High frequency operation
- Low power loss, less RFI and EMI
- Low I<sub>R</sub> value
- High surge capacity
- Epitaxial chip construction





Product Summary	
VR	200 V
IF(AV)	30A
trr	23 ns

### **Description/Applications**

These diodes are optimized to less losses and EMI/RFI in high frequency power conditioning system. The soft recovery behavior of the diodes offers the need as snubber in most applications. These devices are ideally suited for HF welding power converters and other applications where the switching losses are not significant portion of the total losses.

Absolute Maximum Ratings				
Parameter	Symbol	Test Conditions	Values	Units
Repetitive peak reverse voltage	Vrrm		200	V
Continuous forward current	lf(AV)	Tc =110°C	30	
Single pulse forward current	Ifsm	Tc =25°C	300	A
Maximum repetitive forward current	Ifrm	Square wave, 20kHZ	240	
Operating junction	Тј		175	°C
Storage temperatures	Tstg		-55 to +175	°C

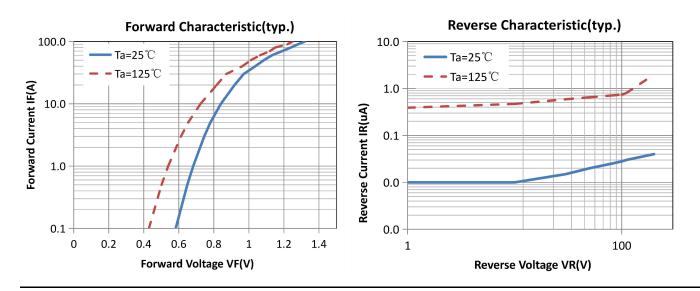


Parameter	Symbol	Test Conditions	Min	Тур.	Max.	Units
Breakdown voltage Blocking voltage	Vbr, Vr	Ir=100#A	200			
Forward voltage (Per Diode)		IF=30 A		0.97	1.20	V
	VF	I⊧=30 A, Tj =125°C		0.87	1.00	
Reverse leakage		Vr= Vrrm			10	
current(Per Diode)	Tj=150°C, Vr=200V			100	μ <b>A</b>	
Reverse recovery time(Per Diode)		I <sub>F</sub> =0.5A, I <sub>R</sub> =1A, I <sub>RR</sub> =0.25A		35	45	
	trr	I <sub>F</sub> =1A,V <sub>R</sub> =30V, di/ <i>dt</i> =200A/us		23	40	ns

## **Thermal characteristics**

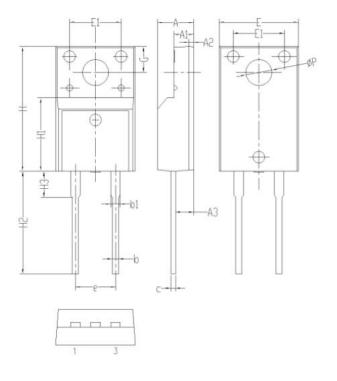
Paramter	Symbol	Тур	Units
Junction-to-Case	R <sub>ejc</sub>	2.0	°C/W

# **Electrical performance (typic)**





# Package Information



#### TO-220F-2 PACKAGE

Symbol	Dimensions	(millimeters)
Symbol	Min.	Max.
А	4.35	4.75
A1	2.30	2.70
A2	0.40	0.80
A3	2.10	2.50
b	0.60	1.00
b1	1.00	1.40
С	0.30	0.70
е	4.60	5.40
E	9.80	10.2
E1	6.30	6.70
Н	15.6	16.0
H1	8.80	9.20
H2	12.9	13.5
H3	3.10	3.50
G	3.10	3.50
ФР	3.10	3.50